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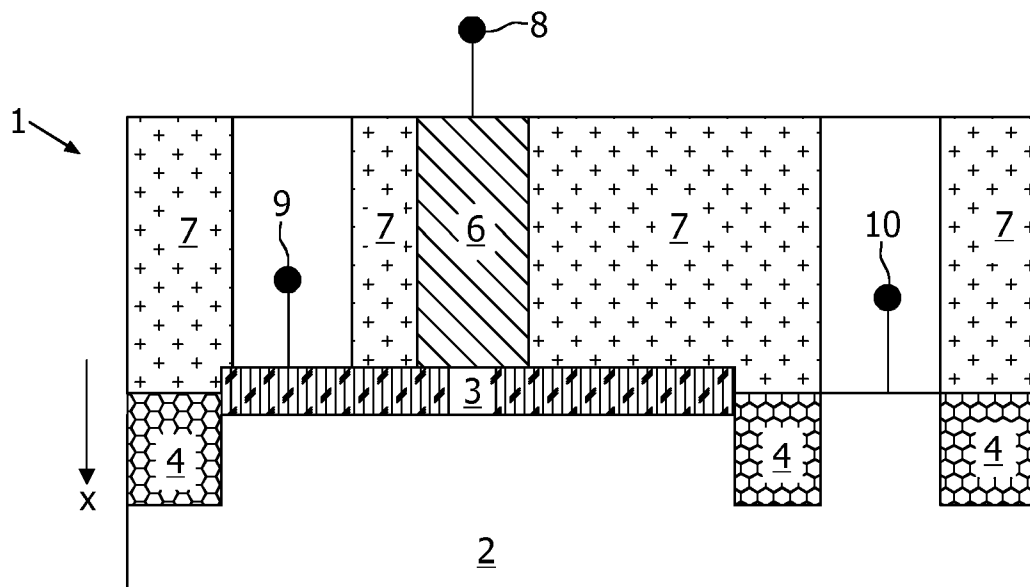
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(54) **Title:** METAL-BASE NANOWIRE TRANSISTOR



(57) **Abstract:** A metal-base transistor is suggested. The transistor comprises a first and a second electrode (2, 6) and base electrode (6) to control current flow between the first and second electrode. The first electrode (2) is made from a semiconduction material. The base electrode (3) is a metal layer deposited on top of the semiconducting material forming the first electrode. According to the invention the second electrode is formed by a semiconducting nanowire (6) being in electrical contact with the base electrode (3).